



## GVBL-T12GD

- PN-type Photodiode
- Indium Gallium Nitride Based Material
- 330 – 445 nm
- Photovoltaic Operation Mode
- TO-46 Package



### Description

**GVBL-T12GD** is a Photodiode working in the spectral range of 330 – 445 nm. It contains an Indium Gallium Nitride based chip die, housed into TO-46 package. It is a great solution, as example for applications like blue LED monitoring, UV curing or UV LED monitoring.

### Absolute Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse Voltage	$V_R$	5	V
Forward Current	$I_{OP}$	1	mA
Operating Temperature	$T_{CASE}$	-30 – +85	°C
Storage Temperature	$T_{STG}$	-40 – +90	°C
Soldering Temperature *	$T_{SLD}$	260	°C

\* must be completed within 10 seconds

### Electro-Optical Characteristics

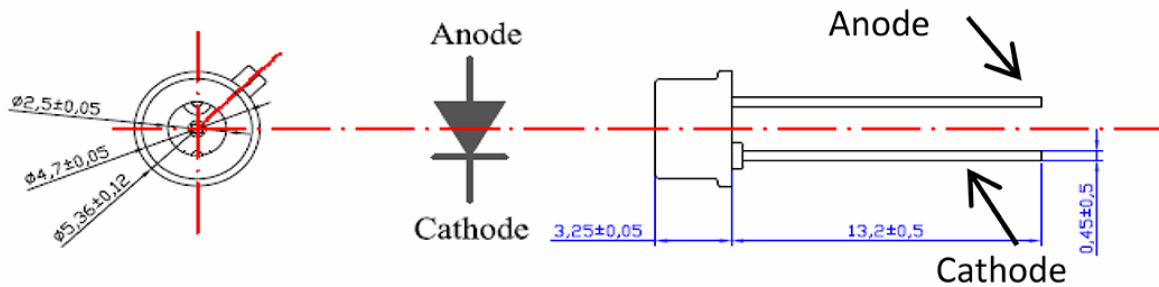
$T_{CASE} = 25^{\circ}C$

Parameter	Symbol	Values	Unit
Dark Current ( $V_R=0.1V$ )	$I_D$	max. 1	nA
Photo Current (LED 385nm, 1mW/cm <sup>2</sup> )	$I_{PH}$	typ. 550	nA
Responsivity (385nm, $V_R=0V$ )	$R$	typ. 0.13	A/W
Spectral Detection Range	$\lambda$	330 – 445	nm
Active Area	$A$	0.0162	mm <sup>2</sup>



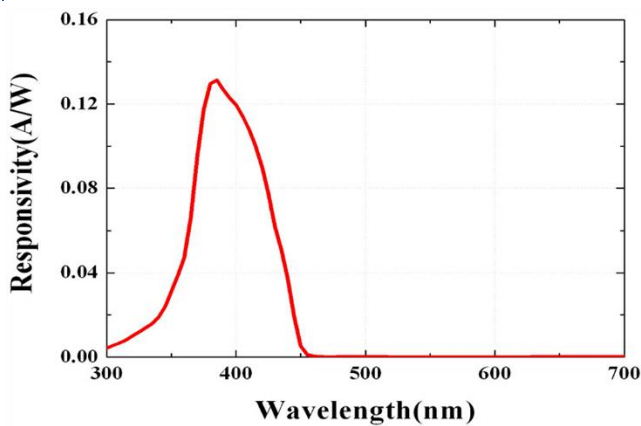
## Outline Dimensions

### GVBL-T12GD

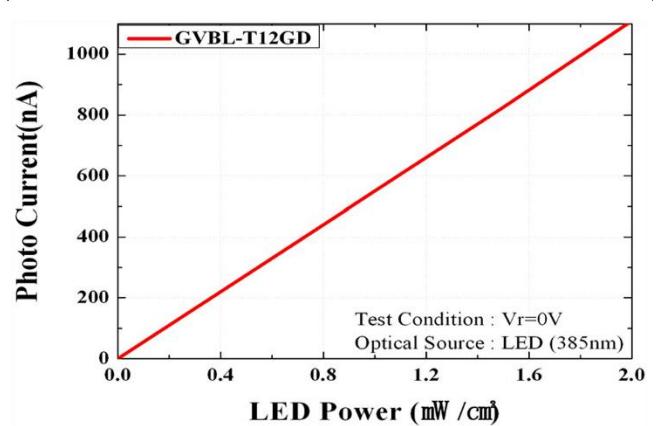


## Typical Performance Curves

### Relative Responsivity



### Photocurrent along LED Power



## Caution

ESD can damage the device hence please avoid ESD.

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